

4N47
4N48
4N49
JAN, JANTX, JANTXV, SINGLE CHANNEL OPTOCOUPLERS
Mii
**OPTOELECTRONIC
PRODUCTS{PRIVATE}
DIVISION**
Features:

- High Reliability
- Base lead provided for conventional transistor biasing
- Rugged package
- High gain, high voltage transistor
- +1kV electrical isolation

Applications:

- Eliminate ground loops
- Level shifting
- Line receiver
- Switching power supplies
- Motor control

DESCRIPTION

Gallium Aluminum Arsenide (GaAlAs) infrared LED and a high gain N-P-N silicon phototransistor packaged in a hermetically sealed TO-5 metal can. The **4N47**, **4N48** and **4N49**'s can be tested to customer specifications, as well as to MIL-PRF-19500 JAN, JANTX, JANTXV and JANS quality levels.

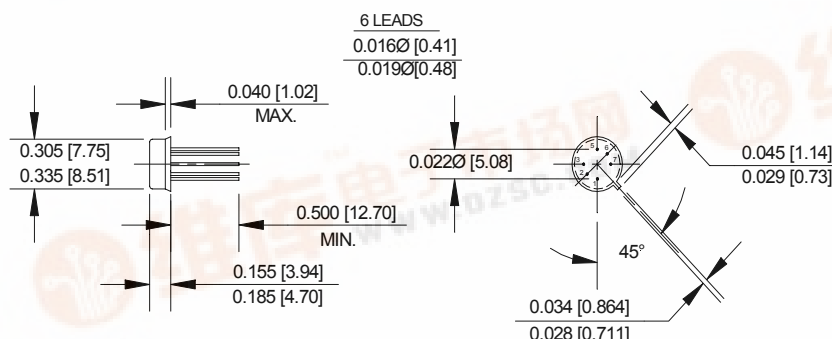
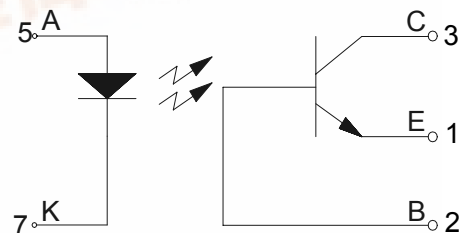
***ABSOLUTE MAXIMUM RATINGS**

Input to Output Voltage	1kV
Emitter-Collector Voltage	7V
Collector-Emitter Voltage (Value applies to emitter-base open-circuited & the input-diode equal to zero)	40V
Collector-Base Voltage	45V
Reverse Input Voltage	2V
Input Diode Continuous Forward Current at (or below) 65°C Free-Air Temperature (see note 1)	40mA
Peak Forward Input Current (Value applies for $t_w \leq 1\mu s$, PRR < 300 pps)	1A
Continuous Collector Current	50mA
Continuous Transistor Power Dissipation at (or below) 25°C Free-Air Temperature (see Note 2)	300mW
Storage Temperature	-65°C to +125°C
Operating Free-Air Temperature Range	-55°C to +125°C
Lead Solder Temperature (1/16" (1.6mm) from case for 10 seconds)	240°C

Notes:

1. Derate linearly to 125°C free-air temperature at the rate of 0.67 mA/°C above 65°C.
2. Derate linearly to 125°C free-air temperature at the rate of 3 mW/°C.

*JEDEC registered data

Package Dimensions

Schematic Diagram


NOTE: ALL LINEAR DIMENSIONS ARE IN INCHES (MILLIMETERS)

4N47, 4N48, and 4N49**JAN, JANTX, JANTXV, JANS, SINGLE CHANNEL OPTOCOUPLED*****ELECTRICAL CHARACTERISTICS** $T_A = 25^\circ\text{C}$ Unless otherwise specified

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Input Diode Static Reverse Current	I_R			100	μA	$V_R = 2\text{V}$	
Input Diode Static Forward Voltage	V_F	1.0	1.4	1.7	V	$I_E = 10\text{mA}$	
-55°C		0.8		1.5			
+25°C		0.7		1.3			
+100°C							

***OUTPUT TRANSISTOR** $T_A = 25^\circ\text{C}$ Unless otherwise specified

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	45			V	$I_C = 100\mu\text{A}, I_B = 0, I_F = 0$	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C = 1\text{mA}, I_B = 0, I_F = 0$	
Emitter-Collector Breakdown Voltage	$V_{(BR)EBO}$	7			V	$I_C = 0, I_E = 100\mu\text{A}, I_F = 0$	

***COUPLED CHARACTERISTICS** $T_A = 25^\circ\text{C}$ Unless otherwise specified

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
On State Collector Current	$I_{C(ON)}$	0.5		5	mA	$V_{CE} = 5\text{V}, I_B = 0, I_F = 1\text{mA}$	
4N47		1.0		10			
4N48		2.0					
4N49							
On State Collector Current	$I_{C(ON)}$	0.7			mA	$V_{CE} = 5\text{V}, I_B = 0, I_F = 2\text{mA}$	
-55°C		1.4					
4N48		2.8					
4N49							
On State Collector Current	$I_{C(ON)}$	0.5			mA	$V_{CE} = 5\text{V}, I_B = 0, I_F = 2\text{mA}$	2
+100°C		1.0					
4N47		2.0					
4N48							
4N49							
Off State Collector Current	$I_{C(OFF)}$			100	nA	$V_{CE} = 20\text{V}, I_B = 0, I_F = 0\text{mA}$	
+25°C							
Off State Collector Current	$I_{C(OFF)}$			100	μA	$V_{CE} = 20\text{V}, I_B = 0, I_F = 0\text{mA}$	
+100°C							
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$			0.3	V	$I_C = 0.5\text{mA}, I_B = 0, I_F = 2\text{mA}$	
4N47				0.3	V	$I_C = 1\text{mA}, I_B = 0, I_F = 2\text{mA}$	
4N48				0.3	V	$I_C = 2\text{mA}, I_B = 0, I_F = 2\text{mA}$	
4N49							
Input to Output Resistance	R_{I-O}	10^{11}				$V_{IN-OUT} = 1\text{kV}$	1
Input to Output Capacitance	C_{I-O}			5	pF	$f = 1\text{MHz}, V_{IN-OUT} = 1\text{kV}$	1
Rise Time/ Fall Time	t_r / t_f			20	μs	$V_{CC} = 10\text{V}, I_F = 10\text{mA}, R_L = 100\Omega$	
Phototransistor Operation	t_r / t_f			25	μs		
4N48				25	μs		
4N49							
Rise Time/ Fall Time	t_r / t_f			0.85	μs	$V_{CC} = 10\text{V}, I_F = 10\text{mA}, R_L = 100\Omega$	
Photodiode Operation	t_r / t_f			0.85	μs		
4N47				0.85	μs		
4N48							
4N49							

NOTES:

- These parameters are measured between all phototransistor leads shorted together and with both input diode leads shorted together.
- This parameter measured using pulse techniques $t_w = 100\mu\text{s}$, duty cycle $\leq 1\%$.

RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Input Current, Low Level	I_{FL}	0	100	μA
Input Current, High Level	I_{FH}	2	10	mA
Supply Voltage	V_{CE}	5	10	V

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION
JAN4N47	4N47 Optocoupler, JAN Screening level
JAN4N48	4N48 Optocoupler, JAN Screening level
JAN4N49	4N49 Optocoupler, JAN Screening level
JANTX4N47	4N47 Optocoupler, JANTX Screening level
JANTX4N48	4N48 Optocoupler, JANTX Screening level
JANTX4N49	4N49 Optocoupler, JANTX Screening level
JANTXV4N47	4N47 Optocoupler, JANTXV Screening level
JANTXV4N48	4N48 Optocoupler, JANTXV Screening level
JANTXV4N49	4N49 Optocoupler, JANTXV Screening level
JANS4N47	4N47 Optocoupler, JANS Screening level
JANS4N48	4N48 Optocoupler, JANS Screening level
JANS4N49	4N49 Optocoupler, JANS Screening level

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